

2SK3124

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- No secondary breakdown
- High electrostatic breakdown voltage

■ Applications

- High-speed switching (switching power supply)
- For high-frequency power amplification

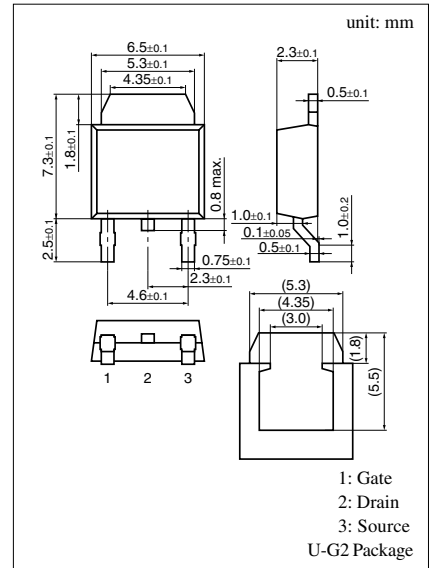
■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit	
Drain to Source breakdown voltage	V_{DSS}	400	V	
Gate to Source voltage	V_{GSS}	± 20	V	
Drain current	DC	I_D	± 0.5 A	
	Pulse	I_{DP}	± 1 A	
Avalanche energy capacity	EAS*	0.25	mJ	
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	10	W
	$T_a = 25^\circ\text{C}$		1	
Channel temperature	T_{ch}	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

* $L = 2\text{mH}$, $I_L = 0.5\text{A}$, 1 pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 320\text{V}$, $V_{GS} = 0$			10	μA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0$			± 1	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	400			V	
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	1		3	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 0.1\text{A}$		17	23	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 0.1\text{A}$	100	160		mS	
Diode forward voltage	V_{DSF}	$I_{DR} = 0.1\text{A}$, $V_{GS} = 0$			-1.5	V	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		48		pF	
Output capacitance (Common Source)	C_{oss}				10		pF
Reverse transfer capacitance (Common Source)	C_{rss}				5		pF
Turn-on time (delay time)	$t_{d(on)}$	$V_{DD} = 100\text{V}$, $I_D = 0.1\text{A}$ $V_{GS} = 10\text{V}$, $R_L = 1\Omega$		65		ns	
Rise time	t_r			35		ns	
Fall time	t_f			40		ns	
Turn-off time (delay time)	$t_{d(off)}$			70		ns	
Thermal resistance between channel and case	$R_{th(ch-c)}$				12.5	$^\circ\text{C/W}$	
Thermal resistance between channel and atmosphere	$R_{th(ch-a)}$				125	$^\circ\text{C/W}$	



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